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Weijian Yang *(University of California at Davis)*
Chris Chase *(Bandwidth10, Inc.)*

TuP48: A New Method to Evaluate the Degree of Potential Fluctuation in InGaN Quantum-Well Laser Diodes by Optical-Pump Stimulated-Emission Measurements (Page 209)
I. Oshima *(Kanazawa Institute of Technology)*
Y. Ikeda *(Kanazawa Institute of Technology)*
S. Sakai *(Kanazawa Institute of Technology)*
A. A. Yamaguchi *(Kanazawa Institute of Technology)*
Y. Kanitani *(Sony Corporation)*
S. Tomiya *(Sony Corporation)*

TuP49: High Speed Wavelength Tuning of MEMS VCSEL with Advanced Voltage Drive Technique (Page 211)
Shunya Inoue *(Tokyo Institute of Technology)*
Shun Nishimura *(Tokyo Institute of Technology)*
Masanori Nakahama *(Tokyo Institute of Technology)*
Akihiro Matsutani *(Tokyo Institute of Technology)*
Fumio Koyama *(Tokyo Institute of Technology)*

Session WA: Plenary III — 8:30 am-9:45 am — Mesa Ballroom

WA1: Opportunities in Semiconductor Laser Technology for Meeting the Requirements of Future High Energy Laser Missions (Page NA)
Paul Leisher *(Lawrence Livermore National Laboratory)*

WA2: Analysis and Design of Semiconductor Lasers Using Strain (Page NA)
Alf Adams *(University of Surrey)*

Session WB: Novel Lasers and Materials — 10:15 am-12:15 pm — Mesa Ballroom

WB1: Non-Reciprocal Lasing from Topological Cavities (Page NA)
Boubacar Kante *(University of California San Diego)*

WB2: 7W CW Operation of Double-Lattice Photonic-Crystal Lasers (Page 213)
Menaka De Zoysa *(Kyoto University)*

Masahiro Yoshida *(Kyoto University)*
Kenji Ishizaki *(Kyoto University)*
Bong-Shik Song *(Kyoto University & Sungkyunkwan University)*
Yoshinori Tanaka *(Kyoto University)*
Ranko Hatsuda *(Kyoto University)*
Shin Fukuhara *(Kyoto University)*
Susumu Noda *(Kyoto University)*

Keisuke Watanabe *(Yokohama National University)*
Toshihiko Baba *(Yokohama National University)*

Seth A. Fortuna *(University of California, Berkeley)*
Christopher Heidelberger *(Massachusetts Institute of Technology)*
Eli Yablonovitch *(University of California, Berkeley)*
Eugene A. Fitzgerald *(Massachusetts Institute of Technology)*
Ming C. Wu *(University of California, Berkeley)*

Yoshito Saijo *(Yokohama National University)*
Takumi Watanabe *(Yokohama National University)*
Keisuke Watanabe *(Yokohama National University)*
Yoshiaki Nishijima *(Yokohama National University)*
Toshihiko Baba *(Yokohama National University)*

C. Fuchs *(Philipps-Universität Marburg)*
P. Ludewig *(NAsPIII/V GmbH)*
A. Brüggemann *(Philipps-Universität Marburg)*
A. Ruiz Perez *(NAsPIII/V GmbH)*
M. J. Weseloh *(Philipps-Universität Marburg)*
S. Reinhard *(Philipps-Universität Marburg)*
J. Hader *(Nonlinear Control Strategies, Inc. & University of Arizona)*
J. V. Moloney *(Nonlinear Control Strategies, Inc. & University of Arizona)*
A. Bäumner *(Philipps-Universität Marburg)*
S. W. Koch *(Philipps-Universität Marburg)*
W. Stolz *(Philipps-Universität Marburg)*

Timothy Eales *(University of Surrey)*
Igor P. Marko *(University of Surrey)*
Barnabas A. Ikyo *(University of Surrey)*
Alf R. Adams *(University of Surrey)*
Alexander Andrejew *(Technische Universität München)*
Kristijonas Vizbaras *(Technische Universität München)*
Markus-C. Amann *(Technische Universität München)*
Leon Shterengas *(State University of New York at Stony Brook)*
Stephen J. Sweeney *(University of Surrey)*

Session WC: High Power Lasers — 1:30 pm-3:30 pm — Mesa Ballroom

WC1: High Pulse Power Wavelength Stabilized Laser Diodes for Automotive LiDAR (Page 225)

A. Knigge *(Ferdinand-Braun-Institut, Leibniz-Institut für Höchstfrequenztechnik)*
A. Klehr *(Ferdinand-Braun-Institut, Leibniz-Institut für Höchstfrequenztechnik)*
H. Wenzel *(Ferdinand-Braun-Institut, Leibnitz-Institut für Höchstfrequenztechnik)*
A. Zeghuzi *(Ferdinand-Braun-Institut, Leibnitz-Institut für Höchstfrequenztechnik)*
J. Fricke *(Ferdinand-Braun-Institut, Leibniz-Institut für Höchstfrequenztechnik)*
A. Maaßdorf *(Ferdinand-Braun-Institut, Leibniz-Institut für Höchstfrequenztechnik)*
A. Liero *(Ferdinand-Braun-Institut, Leibniz-Institut für Höchstfrequenztechnik)*
G. Tränkle *(Ferdinand-Braun-Institut, Leibniz-Institut für Höchstfrequenztechnik)*

WC2: Tapered Monolithic Mode-Locked Laser Diode with 200 PJ Pulse Energy for Space Applications (Page 227)

M. Krakowski *(III-V Lab)*
P. Resneau *(III-V Lab)*
M. Garcia *(III-V Lab)*
E. Vinet *(III-V Lab)*
Y. Robert *(III-V Lab)*
C. Theveneau *(III-V Lab)*
M. Lecomte *(III-V Lab)*
O. Parillaud *(III-V Lab)*
B. Gerard *(III-V Lab)*
S. Kundermann *(Centre Suisse d'Electronique et de Microtechnique SA (CSEM))*
N. Torcheboeuf *(Centre Suisse d'Electronique et de Microtechnique SA (CSEM))*
D. L. Boiko *(Centre Suisse d'Electronique et de Microtechnique SA (CSEM))*

WC3: High Power and High Beam Quality VCSEL Amplifier (Page 229)

Zeuku Ho *(Tokyo Institute of Technology)*
Junichiro Hayakawa *(Fuji Xerox Co., Ltd.)*
Keisuke Shimura *(Tokyo Institute of Technology)*
Keisuke Kondo *(Tokyo Institute of Technology)*
Xiaodong Gu *(Tokyo Institute of Technology)*
Akihiro Matsutani *(Tokyo Institute of Technology)*
Akemi Murakami *(Fuji Xerox Co., Ltd.)*
Fumio Koyama *(Tokyo Institute of Technology)*

WC4: Reliable 2 W DBR-Tapered Diode Lasers Lasing at 1180 nm Based on Highly Strained Quantum Wells (Page 231)

K. Paschke *(Ferdinand-Braun-Institut Leibniz-Institut für Höchstfrequenztechnik)*
G. Blume *(Ferdinand-Braun-Institut Leibniz-Institut für Höchstfrequenztechnik)*
A. Ginolas *(Ferdinand-Braun-Institut Leibniz-Institut für Höchstfrequenztechnik)*
D. Feise *(Ferdinand-Braun-Institut Leibniz-Institut für Höchstfrequenztechnik)*
W. John *(Ferdinand-Braun-Institut Leibniz-Institut für Höchstfrequenztechnik)*
N. Werner *(Ferdinand-Braun-Institut Leibniz-Institut für Höchstfrequenztechnik)*
F. Bugge *(Ferdinand-Braun-Institut Leibniz-Institut für Höchstfrequenztechnik)*
B. Sumpf *(Ferdinand-Braun-Institut Leibniz-Institut für Höchstfrequenztechnik)*

WC5: Failure Mode and Lifetime Analysis of 9×× nm High Power Broad Stripe Laser Diodes (Page 233)

Session WD: Datacom VCSELs and Post Deadline — 4:00 pm-5:45 pm — Mesa Ballroom

WD1: How Ethernet Standards Shaped VCSEL Technology (Page 239)
Jack Jewell *(GreenVCSEL)*

WD2: Vertical-Cavity Silicon-Integrated Lasers by Bonding and Transfer Printing (Page 241)
E. P. Haglund *(Chalmers University of Technology)*
S. Kumari *(Ghent University)*
J. Goyvaerts *(Ghent University)*
J. S. Gustavsson *(Chalmers University of Technology)*
R. G. Baets *(Ghent University)*
G. Roelkens *(Ghent University)*
A. Larsson *(Chalmers University of Technology)*

WD3: Enhanced Digital Modulation of Coherent Photonic Crystal VCSEL Arrays (Page 243)
Harshil Dave *(University of Illinois Urbana-Champaign)*
Peicheng Liao *(University of Southern California)*
Stewart T. M. Fryslie *(Freedom Photonics)*
Zihe Gao *(University of Illinois Urbana-Champaign)*
Bradley J. Thompson *(University of Illinois Urbana-Champaign)*
Alan E. Willner *(University of Southern California)*
Kent D. Choquette *(University of Illinois Urbana-Champaign)*

WD4: 35 GHz Bandwidth with Directly Current Modulated 980 nm Oxide Aperture Single Cavity VCSELs (Page 245)
Nasibeh Haghighi *(Technische Universtität Berlin)*
Gunter Larisch *(Technische Universtität Berlin)*
Ricardo Rosales *(Technische Universtität Berlin)*
Martin Zorn *(JENOPTIK Diode Lab GmbH)*
James A. Lott *(Technische Universität Berlin)*

PD1: Continuous Tuning of Gain Peak Linewidth Enhancement Factor from Negative to Positive with p Doping in InAs QD Laser on Si (Page 247)
Zeyu Zhang *(University of California, Santa Barbara)*
Daehwan Jung *(University of California, Santa Barbara)*
Justin C. Norman *(University of California, Santa Barbara)*
Pari Patel *(University of California, Santa Barbara)*
Weng W. Chow *(Sandia National Laboratories,)*
John E. Bowers *(University of California, Santa Barbara)*